74HC1G08; 74HCT1G08

2-input AND gate Rev. 04 — 17 July 2007

Product data sheet

General description 1.

74HC1G08 and 74HCT1G08 are high-speed, Si-gate CMOS devices. They provide a 2-input AND function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC08 and 74HCT08.

2. **Features**

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

Ordering information

Table 1. **Ordering information**

Type number	Package							
	Temperature range	Name	Description	Version				
74HC1G08GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1				
74HCT1G08GW			body width 1.25 mm					
74HC1G08GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753				
74HCT1G08GV								

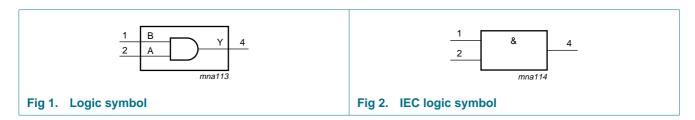
Marking

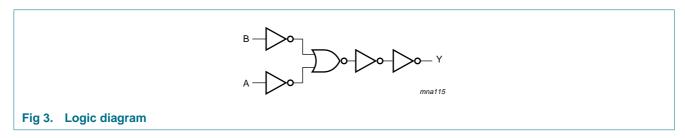
Table 2. **Marking codes**

Type number	Marking
74HC1G08GW	HE
74HCT1G08GW	TE
74HC1G08GV	H08
74HCT1G08GV	T08



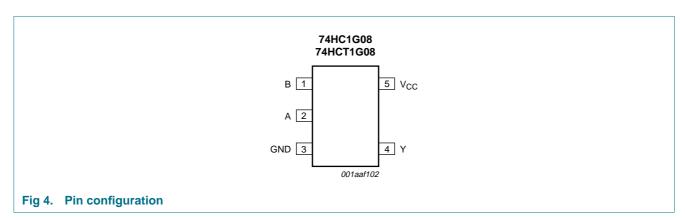
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
В	1	data input
A	2	data input
GND	3	ground (0 V)
Υ	4	data output
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Input		Output
Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I _{CC}	supply current		-	25	mA
I_{GND}	ground current		-25	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	200	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	ymbol Parameter Conditions		74HC1G08			74HCT1G08			Unit
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_{I}	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_{O}	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 \text{ V}$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

^[2] Above 55 $^{\circ}\text{C}$ the value of P $_{tot}$ derates linearly with 2.5 mW/K.

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	
For type	74HC1G08			'		•		
V_{IH}	HIGH-level input	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
	voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V_{IL}	LOW-level input	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
	voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
V_{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	V
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V_{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 20 \mu A$; $V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A$; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A$; $V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
		$I_{O} = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	1.0	-	1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μΑ
Cı	input capacitance		-	1.5	-	-	-	pF
For type	74HCT1G08							
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	8.0	V
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_{O} = -20 \mu A$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	V
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 20 \mu A$; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	V
		$I_{O} = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μΑ

Table 7. Static characteristics ... continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol Parameter		Conditions	–40 °C to +85 °C			–40 °C t	Unit	
			Min	Тур	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	10	-	20	μΑ
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $V_I = V_{CC} - 2.1 \text{ V};$ $I_O = 0 \text{ A}$	-	-	500	-	850	μΑ
C _I	input capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f \le 6.0$ ns; All typical values are measured at $T_{amb} = 25$ °C. For test circuit see Figure 6

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	-40 °C t	Unit	
				Min	Тур	Max	Min	Max	
For type	74HC1G08					'		1	
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		-	25	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	9	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	7	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		-	8	20	-	23	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}$	[2]	-	19	-	-	-	pF
For type	74HCT1G08								
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	11	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	11	-	-	-	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	[2]	-	21	-	-	-	pF

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz

f_o = output frequency in MHz

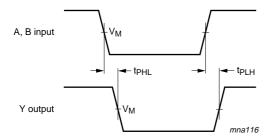
C_L = output load capacitance in pF

 V_{CC} = supply voltage in Volts

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$

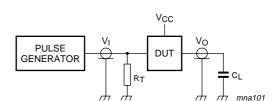
^[2] $\,$ $\,$ $\,$ $\,$ $\,$ $\,$ $\,$ $\,$ C_{PD} is used to determine the dynamic power dissipation P_D (μ W).

12. Waveforms



For 74HC1G08: V_M = 0.5 × V_{CC} ; V_I = GND to V_{CC} For 74HC11G08: V_M = 1.3 V; V_I = GND to 3.0 V

Fig 5. The input (A and B) to output (Y) propagation delays



Test data is given in <u>Table 8</u>. Definitions for test circuit:

 C_L = Load capacitance including jig and probe capacitance

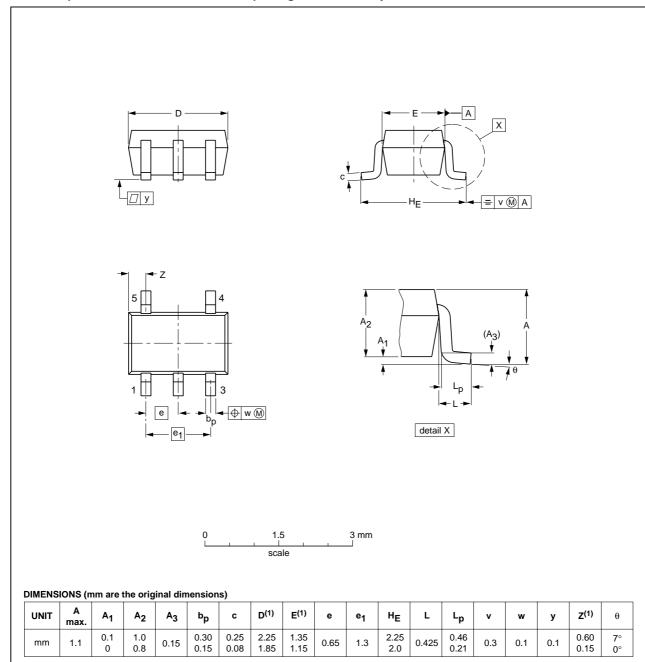
 $R_T = \mbox{Termination resistance}$ should be equal to the output impedance Z_o of the pulse generator

Fig 6. Load circuitry for switching times

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	REFERENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT353-1		MO-203	SC-88A			00-09-01 03-02-19	

Fig 7. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

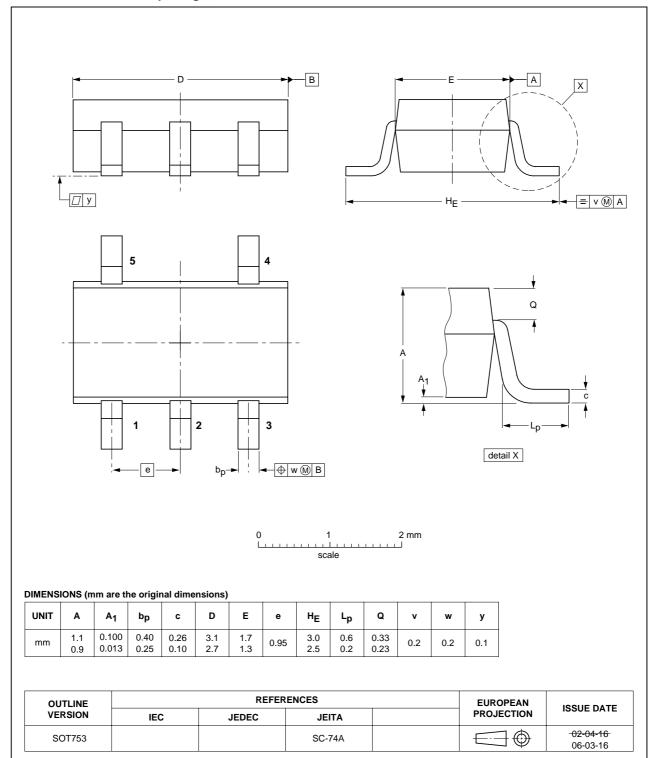


Fig 8. Package outline SOT753 (SC-74A)

14. Abbreviations

Table 9. Abbreviations

Acronym	Description
DUT	Device Under Test
TTL	Transistor-Transistor Logic

15. Revision history

Table 10. Revision history

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uick Reference Data ar	nd Soldering section	ns removed.	
ection 2 "Features" upd	ated.		
517 Product sp	ecification	-	74HC_HCT1G08_2
302 Product sp	ecification	-	74HC_HCT1G08_1
110 Preliminary	y specification	-	-
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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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